

# ILC ECAL activities at Tokyo

Komamiya-lab (Dept. of Physics):

on **silicon ECAL**:

Sachio KOMAMIYA,  
Daniel JEANS,  
Yoshio KAMIYA,  
Shion CHEN,  
Chihiro KOZAKAI

(also: Ultra Cold Neutron experiments,  
ATLAS, Shintake monitor@ATF2)

activities

Silicon sensor electrical measurements  
SiECAL optimisation simulation studies  
Physics proto testbeam data analysis

Ootani-lab (ICEPP):

on **scintillator ECAL**:

Wataru OOTANI,  
Sei IEKI (“seconded” from  
Satoru Yamashita's lab)

(also: MEG experiment)

Scintillator strip optimisation  
MPPC development

# Near-term plans for SiECAL side

## Hardware (led by Yoshio Kamiya):

Measure radiation tolerance to sensors to neutrons

Suitable reactor identified in Japan (good for baby chip)

I-V, C-V, cosmic/source signal before and after radiation

## Issues/questions

Would like to read sensor signals with full DAQ system

(by-products:

learn how to use system,

develop into cosmic/beam ASU calibration system)

Need help from Fr to get pieces

In parallel, look for PCB producer for FeVx

Which version?

Maybe start with conservative design,

later investigate more aggressive one?

Need design files from Omega / LLR

To instrument the PCB, need some SKIROC ASICs

# Near-term plans for SiECAL side

## Optimisation/Software (led by Daniel)

2-particle separation (photon-photon, photon-pion)

ILD simulation – different ECAL models

CALICE data & simulation

Using PandoraPFA (started) and GARLIC (planned)

GARLIC photon finding algorithm development

have some ideas for improvements

Questions:

define “default” ECAL

(maybe wait for re-baselined ILD models before doing too much)

which parameters to change

is our current cross-talk modeling good enough?

What is realistic/expected intra-channel xtalk level?

## Other more general ideas/questions

If statement of interest for hosting ILC arrives (and it may arrive soon), we should have some procedure by which groups can join us, and a list of open work packages we can ask them to choose from

This procedure will also help us to better organise our effort

We may want to be more proactive about inviting groups

University, lab seminars

for now, focus on Japan/Korea/China and Europe?

(at least while there are 2 detectors...)

Need detailed cost model for silicon:

silicon cost proportional to # wafers, not silicon area

-> cost-efficient detector length is quantised

Should we set up some external review of project at this stage?

# Proposals for more realistic (pessimistic?) ILD ECAL simulation and digitisation

Daniel Jeans, October 2013  
with input from many others, thanks!

Current Mokka models probably too optimistic from a technical point of view.

Try to agree among ourselves on realistic (pessimistic) scenarios

Ensure that simulations are at a **similar level of realism**:  
fairer comparisons between technologies,  
more confidence in their conclusions

I consider only the internal ECAL parameters, not the overall size.  
(which is an important parameter, but not related to realism of simulation)

Consider Si and Sc technologies with **same total ECAL thickness**  
to avoid biasing cost of outer detector parts

Starting point: ILD\_o1\_v05 and ILD\_o3\_v05

Internal ECAL parameters.

(all dims in mm)	Si / Sc thickness	Number of W layers, thickness	Equipped PCB thickness	Cell (strip) size	Guard ring (reflector) Thickness	Total thickness
Si-DBD	0.5	20x2.4 9x4.2	0.8	~5x5	0.5	185
Si-A	0.32	17x2.4 8x4.8	2.0	~5x5	0.5	198
Si-B	0.32	13x3.15 6x6.3	3.5	~5x45	0.5	203
Sc-DBD	2.0	20x2.4 9x4.2	0.8	~5x45	0.057	227
Sc	1.0	17x2.4 8x4.8	1.2	~5x45	0.1	195

Hybrid models should use same parameters, where appropriate, and generally aim for a thickness of 200 +/- 5 mm

Digitizer effects to be included:

Si-ECAL:

0.5 MIP cut (will have to change with thinner silicon)

Sc-ECAL:

non-uniformity, attenuation length 500mm

Convert to # photo-electrons (7/MIP), poisson smear

MPPC saturation, effective pixel number = 10000

Cut at 0.5 MIP

Cross-checks: (small dedicated simulation studies)

Effects of:

Realistic noise rate

Calibration/saturation uncertainty

Cross-talk in ASIC/pads/strips

Use measured strip non-uniformity